



### CST3400Q N-Ch 30V Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

#### CST3400Q Product Summary

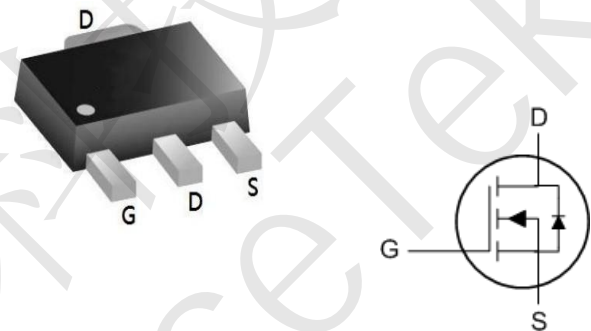


BVDSS	RDSON	ID
30V	20mΩ	7.0A

#### CST3400Q Description

The CST3400Q is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The CST3400Q meet the RoHS and Green Product requirement with full function reliability approved.

#### CST3400Q SOT89-3L Pin Configuration



#### CST3400Q Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.0	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.5	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	25.4	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	2.5	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

#### CST3400Q Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	92	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	---	$^\circ C/W$



### CST3400Q N-Ch 30V Fast Switching MOSFETs

#### CST3400Q Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±12V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.9	1.4	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance note2	V <sub>GS</sub> =10V, I <sub>D</sub> =4.2A	-	20	28	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	25	34	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1A	-	35	50	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHz	-	602	-	pF
C <sub>oss</sub>	Output Capacitance		-	56	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	42	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =15V, I=4A, V <sub>GS</sub> =4.5V	-	4.8	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	1.2	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	1.7	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =15V, I <sub>D</sub> =4A, R <sub>GEN</sub> =3Ω, V <sub>GS</sub> =4.5V	-	12	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	52	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	17	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	10	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	7.0	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	25.2	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =5.8A	-	-	1.2	V

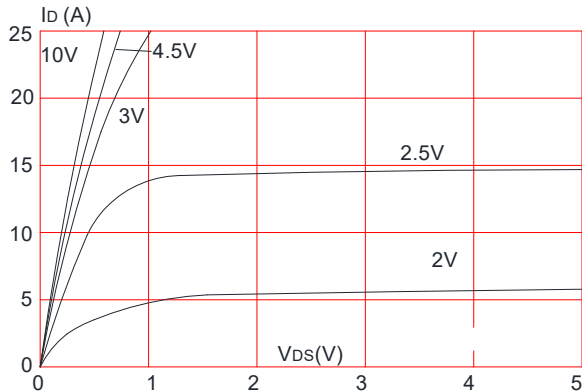
Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

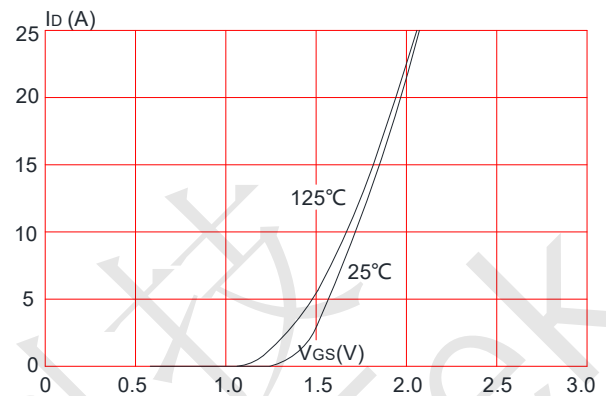


## CST3400Q Typical Performance Characteristics

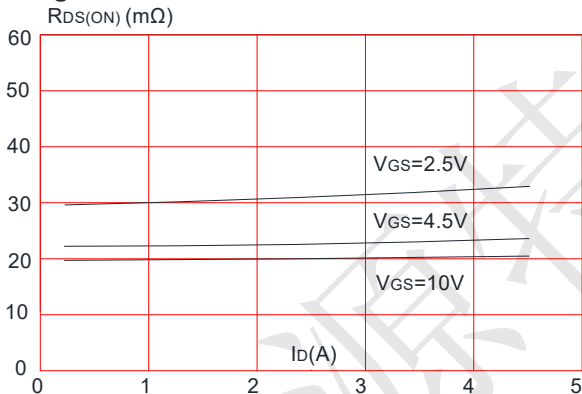
**Figure 1: Output Characteristics**



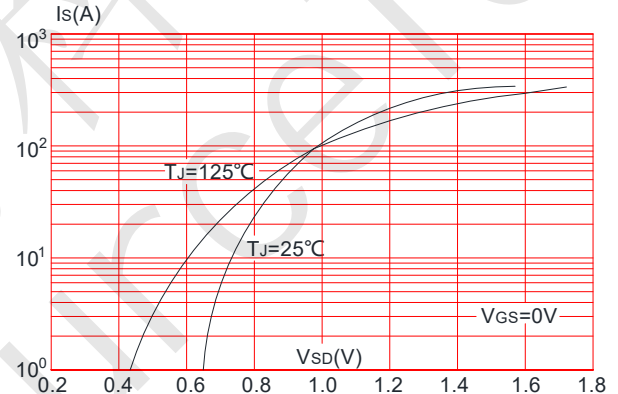
**Figure 2: Typical Transfer Characteristics**



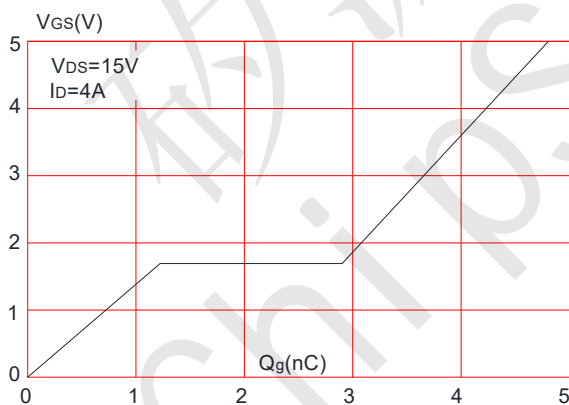
**Figure 3: On-resistance vs. Drain Current**



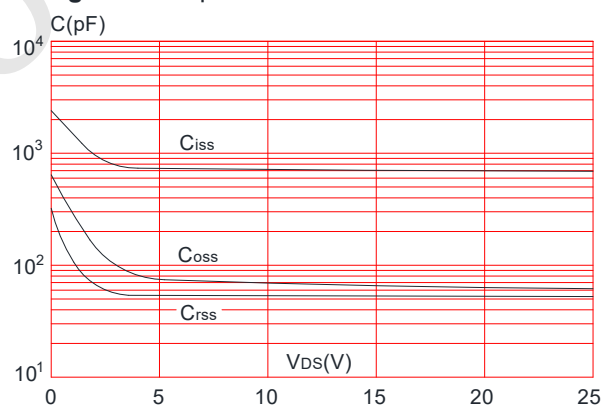
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**



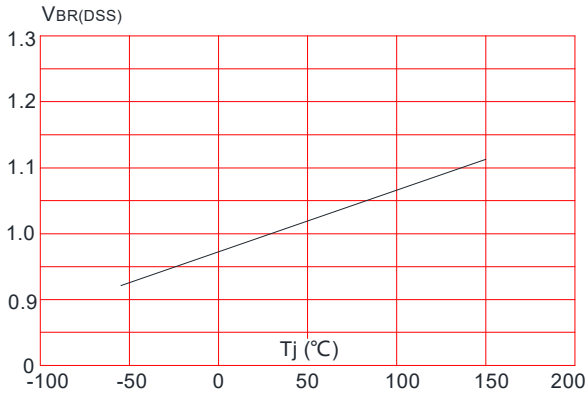
**Figure 6: Capacitance Characteristics**



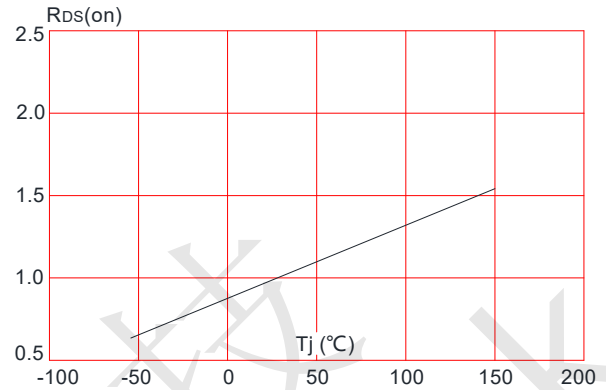


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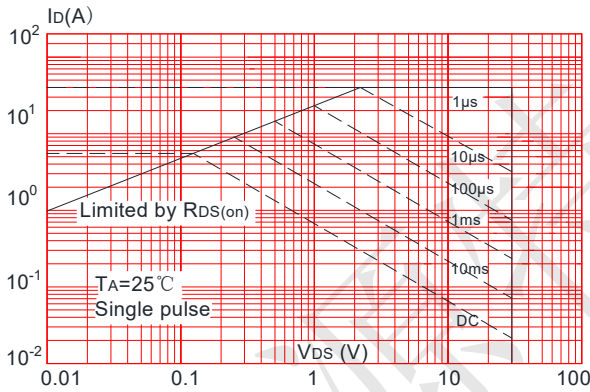
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



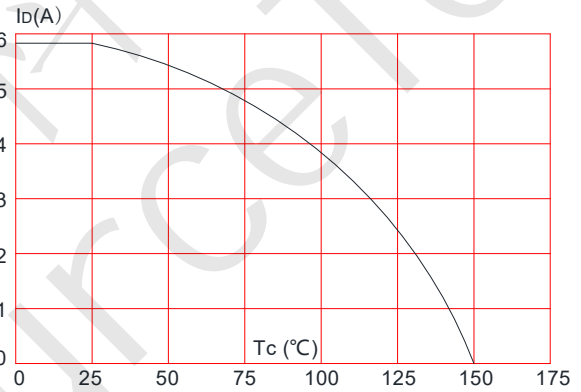
**Figure 8:** Normalized on Resistance vs. Junction Temperature



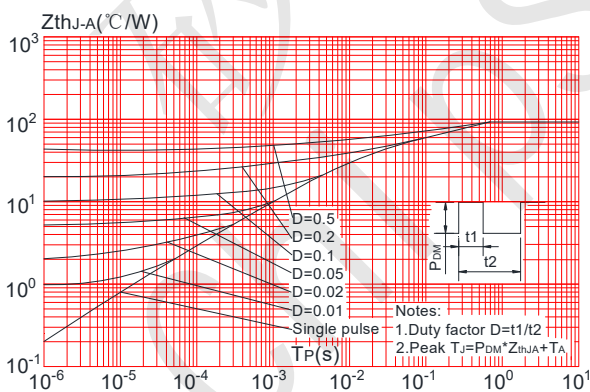
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature

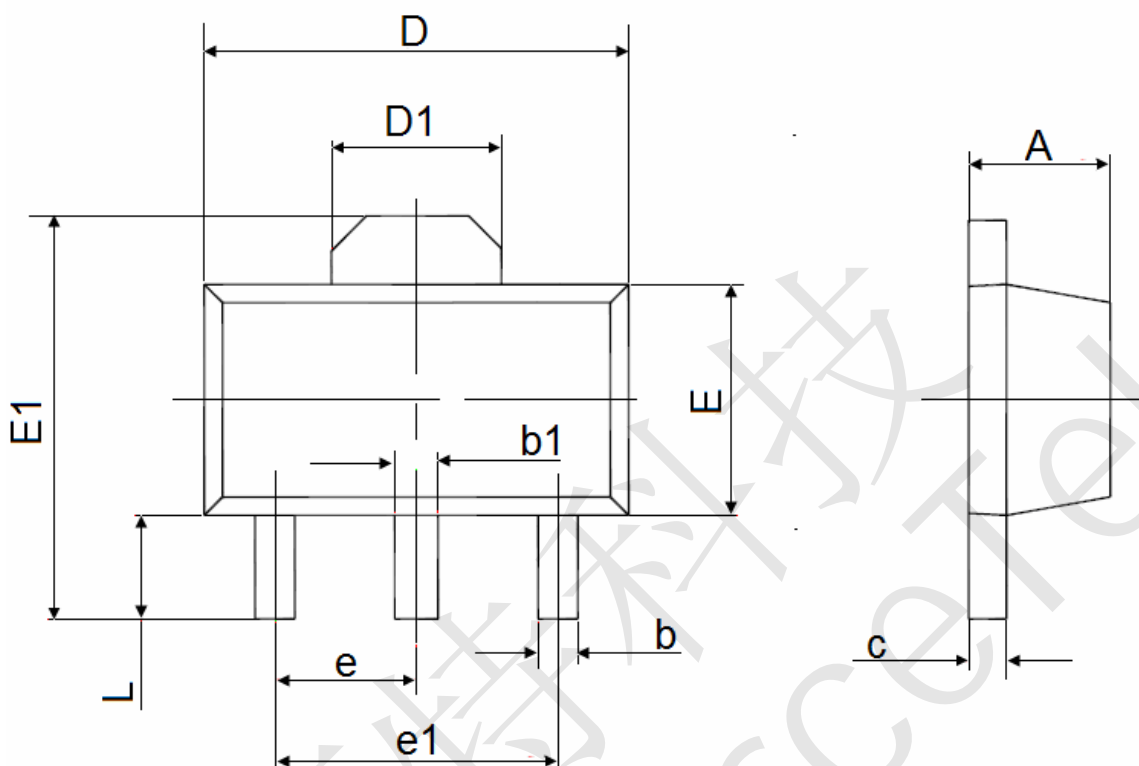


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





CST3400Q SOT-89-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047